L Number	Hits	Search Text	DB	Time stamp
2	2172	(semiconductor adj3 memory) same (cell$2 adj3 block$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:01
3	107	((semiconductor adj3 memory) same (cell$2 adj3 block$2)) same (stor$2 adj3 data)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:00
4	8	(((semiconductor adj3 memory) same (cell$2 adj3 block$2)) same (stor$2 adj3 data)) same redundancy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:00
5	38	(cell adj3 block) same (stor$3 adj3 data) same redundancy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:01
6	6	((cell adj3 block) same (stor$3 adj3 data) same redundancy) and ECC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:01
7	378	((semiconductor adj3 memory) same (cell$2 adj3 block$2)) and 365/200,201,225.7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:01
8	4	(((semiconductor adj3 memory) same (cell$2 adj3 block$2)) and 365/200,201,225.7.ccls.) and redundancy and ECc	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:02
9	14	choi-sung-h.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:02
10	433	choi-sung-$.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:02
11	2	choi-sung.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:02
12	0	(((semiconductor adj3 memory) same (cell$2 adj3 block$2)) and 365/200,201,225.7.ccls.) and ECC and repair	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:04
13	118	(((semiconductor adj3 memory) same (cell$2 adj3 block$2)) and 365/200,201,225.7.ccls.) and repair	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:04
14	94	((((semiconductor adj3 memory) same (cell$2 adj3 block$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:04

15	94	(((((semiconductor adj3 memory) same (cell$2 adj3 block$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc$3) and 365/$7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:04
16	94	(((((semiconductor adj3 memory) same (cell$2 adj3 block$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc$3) and ((semiconductor adj3 memory) same (cell$2 adj3 block$2))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:04
17	3	(((((semiconductor adj3 memory) same (cell$2 adj3 block$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc$3) and (((semiconductor adj3 memory) same (cell$2 adj3 block$2)) same (stor$2 adj3 data))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:05
18	12	((cell adj3 block) same (stor$3 adj3 data) same redundancy) and (((semiconductor adj3 memory) same (cell$2 adj3 block$2)) and 365/200,201,225.7.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:05
19	8	(((cell adj3 block) same (stor$3 adj3 data) same redundancy) and (((semiconductor adj3 memory) same (cell$2 adj3 block$2)) and 365/200,201,225.7.ccls.)) and ((((((semiconductor adj3 memory) same (cell$2 adj3 block$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc$3) and 365/$7.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:05